

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1 (currently amended). A semiconductor device comprising:

a radiating plate;

a semiconductor chip bonded ~~on one side of~~ onto the radiating plate;

a rectangular-shaped resin wall to which surrounds the semiconductor chip bonded to the radiating plate, said rectangular-shaped resin wall having a first pair of opposing sides and a second pair of opposing sides;

a conductive member ~~extended~~ extending through ~~a lower end~~ one of the first pair of opposing sides of the resin wall and retained by the resin wall, which said conductive member is electrically connected to the semiconductor chip; and

a resin lid bonded to an upper end of the resin wall,

~~wherein the lower end of said resin wall in a first area and in the vicinity thereof are bonded to said one side and an end face of said radiating plate, and the lower end of said resin wall in a second area other than said first area and the vicinity thereof is bonded to only said one side of said radiating plate, and~~

 said semiconductor chip is sealed in a space enclosed by said radiating plate, said resin wall and said resin lid,

said radiating plate extends outward of said second pair of opposing sides of said resin wall.

2 (cancelled).

3 (original). The semiconductor device according to claim 1, wherein the resin wall is fitted to protruding parts or recessed parts provided on the radiating plate.

4 (cancelled).

5 (currently amended). The semiconductor device according to claim [[1]] 3, wherein the recessed parts are provided on the opposed side parts of the radiating plate, the protruding parts are protruded and provided on the inner surfaces of the recessed parts, and the lower end part of the resin wall is buried in the recessed parts.

6 (cancelled).

7(currently amended). The semiconductor device according to claim 1, wherein holes are provided in the conductive member and said holes are located in the outside positions of the resin wall on the conductive member.

8 (cancelled).

9 (currently amended). The semiconductor device according to claim 1, wherein first holes are provided in the conductive member and said first holes are located in the outside positions of the resin wall on the conductive member, and second holes or cutouts are provided in the region extending through the resin wall of the conductive member.

10 (cancelled).

11 (original). The semiconductor device according to claim 9, wherein the first holes are arranged so as to overlap the space area between the second holes or cutouts when the conductive member is seen in the resin wall direction from the outside of the resin wall.

12 (cancelled).

13 (original). The semiconductor device according to claim 1, wherein a stepped part to be fitted to the inner periphery of the resin wall is provided on the resin lid.

14 (cancelled).

15 (original). The semiconductor device according to claim 13, wherein the resin lid has a vertically plane symmetric shape.

16 (cancelled).

17 (original). The semiconductor device according to claim 1, wherein the surface of the radiating plate surrounded by the resin wall is surface-finished by silver plating, and the other surface of the radiating plate except the part for bonding the resin wall and the inner lead part and outer lead part of the conductive member are surface finished by gold plating.

18 (cancelled).

19 (withdrawn). A manufacturing method of semiconductor device comprising the steps of:

forming a conductive member by a lead frame;

arranging the lead frame and a radiating plate in a metal mold having a cavity corresponding to a resin wall;

clamping the region of the radiating plate, that region forming the inside of the resin wall, by an upper die and a lower die of the metal mold; and

molding a resin in the metal mold to form the resin wall.

20 (withdrawn). A manufacturing method of semiconductor device comprising the steps of:

forming a conductive member by a lead frame;

forming a radiating plate by use of a metal plate different from the lead frame;

arranging the lead frame and the metal plate within a metal mold having a cavity corresponding to a resin wall;

molding a resin in the metal mold to form the resin wall and opening the mold; and

plating the radiating plate and the conductive member.

21 (withdrawn). A manufacturing method of semiconductor device according to claim 20, wherein the plating step comprising the steps of:

electroplating the radiating plate with silver;

electroplating the conductive member with gold; and

electroplating the region of the radiating plate with gold, the region forming the outside of the resin wall.

22 (previously presented). The semiconductor device according to claim 1, wherein the radiating plate has end portions formed integrally at both ends of a center portion of the radiating plate, the lower end of the resin wall is bonded to said center portion, and said end portions are exposed through the resin wall.

23 (cancelled).

24 (previously presented). The semiconductor device according to claim 1, wherein said conductive member is broader on the inside of said resin wall.

25 (cancelled).